



L Number	Hits	Search Text	DB	Time stamp	<del></del>
5	8		USPAT	2002/11/04	09:43
		or ("6180457") or ("6429470") or		2002, 11, 01	05.45
		("6318267") or ("5572050") or			
		("4775549")).PN.			
18	20		USPAT;	2002/11/04	10:09
		same (ONO or (oxide adj nitride adj	US-PGPUB;		
		oxide))) and (photoresist or mask)	EPO; JPO;		
1			DERWENT;		
19	10	(((ONS or (oxide adj nitride adj silicon))	IBM_TDB USPAT;	2002/11/04	10 10
	1	same (ONO or (oxide adj nitride adj	US-PGPUB;	2002/11/04	10:10
		oxide))) and (photoresist or mask)) and	EPO; JPO;		
		semiconductor	DERWENT;		
			IBM TDB	.	
24	191	(438/201).CCLS.	USPĀT;	2002/11/04	11:17
			US-PGPUB;		
ļ			EPO; JPO;		
			DERWENT;		
_	3	//U6004947U) on /U5104010U)	IBM_TDB	0000/11/01	
	3	(("6004847") or ("5104819") or ("6274428")).PN.	USPAT	2002/11/04	09:43
_	524	(438/255).CCLS.	USPAT;	2002/11/01	10.00
		(	US-PGPUB;	2002/11/01	10.08
1			EPO; JPO;	1	
			DERWENT;		
			IBM TDB		
-	479	(438/258).CCLS.	USPAT;	2002/11/01	10:10
			US-PGPUB;		
			EPO; JPO;		
			DERWENT;		
_	271	(438/261).CCLS.	IBM TDB	2002/11/01	10.10
	2/1	(430/201).CCE3.	USPAT; US-PGPUB;	2002/11/01	10:10
			EPO; JPO;		
			DERWENT;		
]	•		IBM TDB		
-	1104	(438/257).CCLS.	USPAT;	2002/11/01	10:10
			US-PGPUB;		
			EPO; JPO;		
			DERWENT;		
_	450	(438/756).CCLS.	IBM_TDB	2002/11/01	10 11
	150	(430/730/.0003.	USPAT; US-PGPUB;	2002/11/01	10:11
			EPO; JPO;		
			DERWENT;		
			IBM TDB		
-	116	(438/757).CCLS.	USPAT;	2002/11/01	10:11
	i		US-PGPUB;		
			EPO; JPO;		-
			DERWENT;		
_	308	(438/724).CCLS.	IBM_TDB USPAT;	2002/11/01	10.11
	500	(100/124/10000)	USPAT; US-PGPUB;	2002/11/01	10:11
			EPO; JPO;		
			DERWENT;		
			IBM TDB		į
-	3039	438/255,258,201,261,257,756,757,724.ccls.	USPĀT;	2002/11/01	10:15
			US-PGPUB;		
	-		EPO; JPO;		ĺ
]			DERWENT;		
_	14	439/255 259 201 261 257 756 757 724	IBM_TDB	2002/11/05	
	7.4	438/255,258,201,261,257,756,757,724.ccls. and (ONS or (oxide adj nitride adj	USPAT;	2002/11/01	10:17
[		silicon))	US-PGPUB;		
	1		EPO; JPO; DERWENT;		
	ļ		IBM TDB		
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-	1	438/255,258,201,261,257,756,757,724.ccls.	USPAT;	2002/11/01 10:18
		and ((ONS or (oxide adj nitride adj	US-PGPUB;	
		silicon)) same (ONO or (oxide adj nitride	EPO; JPO;	
		adj oxide)))	DERWENT;	
			IBM TDB	
-	24	(ONS or (oxide adj nitride adj silicon))	USPAT;	2002/11/01 10:21
		same (ONO or (oxide adj nitride adj	US-PGPUB;	
		oxide))	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	13	((ONS or (oxide adj nitride adj silicon))	USPAT;	2002/11/04 10:07
		same (ONO or (oxide adj nitride adj	US-PGPUB;	
		oxide))) and semiconductor	EPO; JPO;	
			DERWENT;	
			IBM_TDB	